EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	forster-arnold.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:17
L2	3	lepsa-mihail-ion.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:38
L3	3	stock-jurgen.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:17
L4	2	"6111265".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:42
L5	2	"4945393".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:18
L6	2	"5463275".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:18
L7	0	(n+ adj GaAs) and (graded near AlGaAs) and (n+ adj (layer or film)) and (undoped adj intermediate adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:44
L8	0	(n+ near GaAs) and (graded near AlGaAs) and (n+ adj (layer or film)) and (undoped adj intermediate adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:44

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L9	0	(n+ near GaAs) and (graded near AlGaAs) and (undoped adj intermediate adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:45
L10	1	(GaAs and (gallium adj arsenide)) and (graded near (AlGaAs or (aluminum adj gallium adj arsenide))) and (undoped adj intermediate adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:46
L11	1	(GaAs and (gallium adj arsenide)) and (graded with (AlGaAs or (aluminum adj gallium adj arsenide))) and (undoped adj intermediate adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:46
L12	1	(GaAs and (gallium adj arsenide)) and (graded same (AlGaAs or (aluminum adj gallium adj arsenide))) and (undoped adj intermediate adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:46
L13	12	(GaAs and (gallium adj arsenide)) and (graded same (AlGaAs or (aluminum adj gallium adj arsenide))) and (undoped adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:49
L14	0	(highly adj doped adj (GaAs and (gallium adj arsenide))) and (graded same (AlGaAs or (aluminum adj gallium adj arsenide))) and (undoped adj (GaAs and (gallium adj arsenide)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:50
L15	0	257/006.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:51
L16	215	257/6.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:51

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L17	52	257/7.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 08:51
L18	113	257/8.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 09:31
L19	18	transferred adj electron adj effect adj device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 09:32
L20	163	gunn adj device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 09:37
L21	1846	gunn adj diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 09:37
L22	487	(gunn adj diode) and (gaas or (gallium adj arsenide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 09:38
L23	38	(gunn adj diode) and (gaas or (gallium adj arsenide)) and (algaas or (aluminum adj gallium adj arsenide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 10:01
L24	612	epitaxial adj (gaas or (gallium adj arsenide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 10:02